Switching loss measurement for Wide-bandgap semiconductors



- In switching cell measurement (classic double pulse) for GaN and SiC
- Commutation loop current measurement
 - Low additional inductance of 300 pH
 - Bandwidth of 500 MHz
- High resolution control signal
 - Up to 4 gate signals
 - Configuration script
 - Pulse and dead time resolution of 250 ps
- Coil for measurement purposes
 - Calibrated up to 100 MHz
 - Low stray field due to toroid shape
 - Low HF losses due to litz wire
 - Pulse resistant up to 150 A because no magnetic material is used
- Parameters of the measurement seen in the picture below
 - U DC = 600 V
 - I L = 20 A
 - L = 7 uH
 - dU/dt = 70 V/ns --> 600 V in 8.5 ns !!!
 - dI/dt = 18 A/ns







